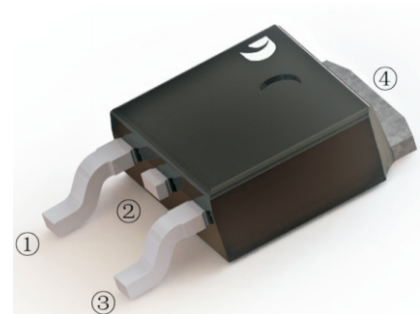


7A, 650V N-CHANNEL POWER MOSFET

TO-252W

DESCRIPTION

The D7N65 is a high voltage power MOSFET combines advanced trench MOSFET designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and high rugged avalanche characteristics. This power MOSFET is usually used in high speed switching applications of switching power supplies and adaptors.



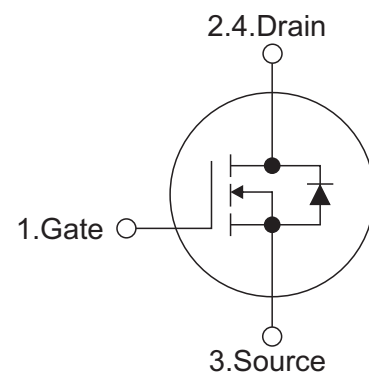
Features

- $R_{DS(ON)} \leq 1.3 \Omega$ @ $V_{GS}=10V, I_D=3.5A$
- Fast switching capability
- Avalanche energy tested
- Improved dv/dt capability, high ruggedness

Mechanical data

- Case: TO-252W
- Approx. Weight: 0.315g (0.011oz)
- Lead free finish, RoHS compliant
- Case Material: "Green" molding compound, UL flammability classification 94V-0, "Halogen-free".

SYMBOL



ABSOLUTE MAXIMUM RATINGS (TA=25°C, unless otherwise specified)

PARAMETER	Symbols	RATINGS	Units
Drain-Source Voltage	V_{DSS}	650	V
Gate-Source Voltage	V_{GSS}	± 30	V
Continuous Drain Current	I_D	$T_c=25^\circ C$	7
		$T_c=100^\circ C$	4.5
Pulsed Drain Current (Note 2)	I_{DM}	28	A
Avalanche Energy Single Pulsed (Note 3)	E_{AS}	281.3	mJ
Peak Diode Recovery dv/dt (Note 4)	dv/dt	50	V/ns
Power Dissipation	P_D	32	W
Operation Junction Temperature and Storage Temperature	T_j, T_{stg}	-55 ~ +150	$^\circ C$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $L = 10mH, I_{AS} = 7.5A, V_{DD} = 50V, R_G = 25 \Omega, \text{Starting } T_J = 25^\circ C$

4. $ISD \leq 7A, di/dt \leq 200A/\mu s, V_{DD} \leq BVDSS, \text{Starting } T_J = 25^\circ C$

THERMAL DATA

PARAMETER	Symbols	RATINGS	Units
Junction to Ambient	R_{thJA}	63	$^\circ C/W$
Junction to Case	R_{thJC}	0.95	$^\circ C/W$



ELECTRICAL CHARACTERISTICS (TA=25°C, unless otherwise specified)

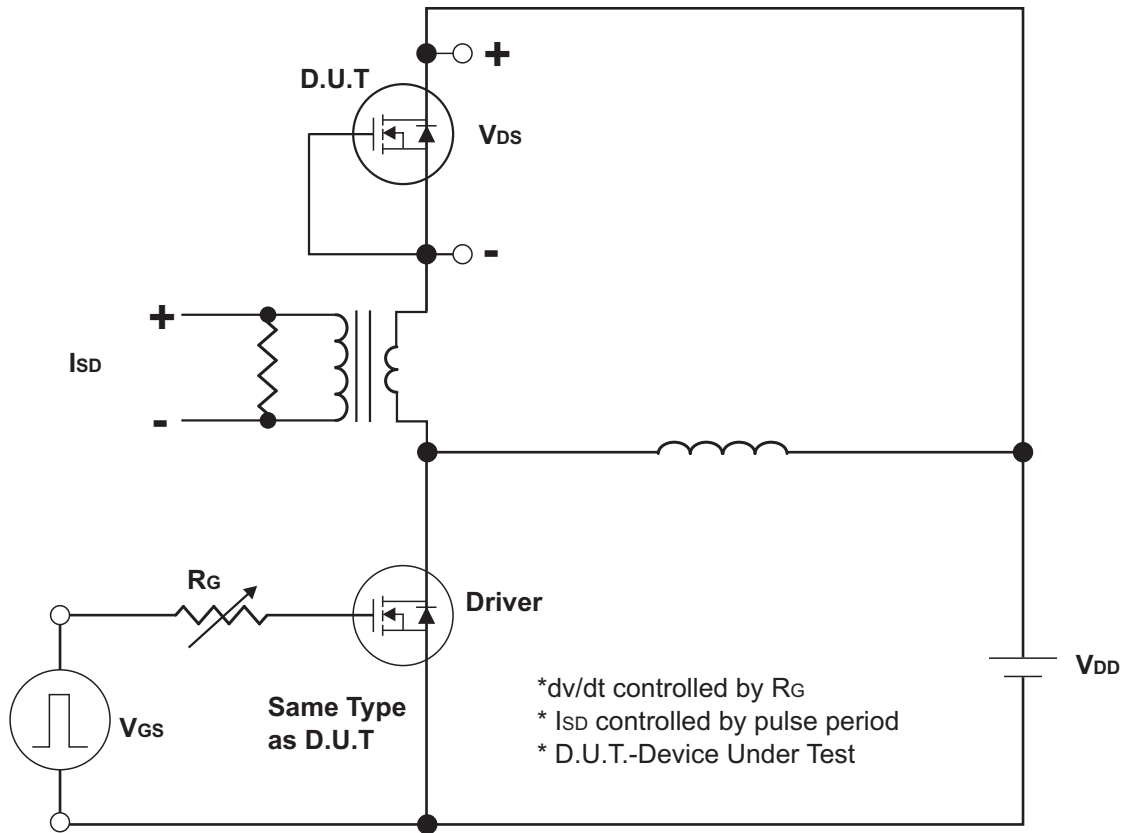
PARAMETER	Symbols	TEST CONDITIONS	Min	Typ	Max	Units
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{DS}=0V, I_D=250\mu A$	650			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=650V, V_{GS}=0V$			1	μA
Gate- Source Leakage Current	Forward	I_{GSS}			100	nA
	Reverse				-100	
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2.0		4.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=3.5A$			1.35	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ISS}	$V_{DS}=25V,$ $V_{GS}=0V,$ $f=1.0MHz$		1080		pF
Output Capacitance	C_{OSS}			90		pF
Reverse Transfer Capacitance	C_{RSS}			2.5		pF
SWITCHING CHARACTERISTICS						
Total Gate Charge (Note 1)	Q_G	$V_{DS}=520V, V_{GS}=10V,$ $I_D=7A, I_G=1mA$ (NOTE1,2)		22		nC
Gate-Source Charge	Q_{GS}			5		nC
Gate-Drain Charge	Q_{GD}			5.5		nC
Turn-On Delay Time (Note 1)	$t_{D(ON)}$	$V_{DS}=100V, V_{GS}=10V,$ $I_D=7A, R_G=25\Omega$ (NOTE1,2)		12		ns
Turn-On Rise Time	t_R			20		ns
Turn-Off Delay Time	$t_{D(OFF)}$			74		ns
Turn-Off Fall Time	t_F			33		ns
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Maximum Body-Diode Continuous Current	I_S				7	A
Maximum Body-Diode Pulsed Current	I_{SM}				14	A
Drain-Source Diode Forward Voltage (Note 1)	V_{SD}	$I_S=7A, V_{GS}=0V$			1.4	V
Reverse Recovery Time (Note 1)	t_{rr}	$I_S=7A, V_{GS}=0V,$ $di/dt=100A/\mu s$		506		ns
Reverse Recovery Charge	Q_{rr}			2.7		μC

Notes:

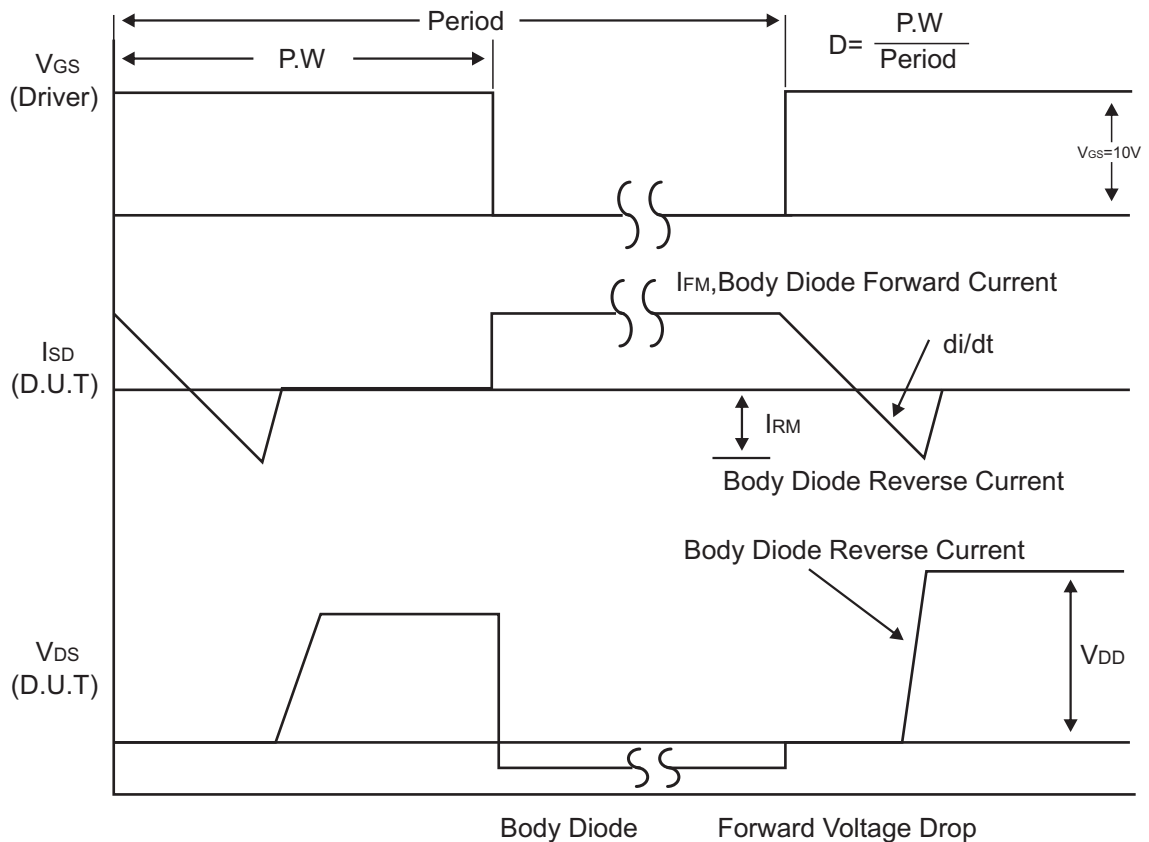
1. Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$.
2. Essentially independent of operating temperature.



Test Circuits and waveforms



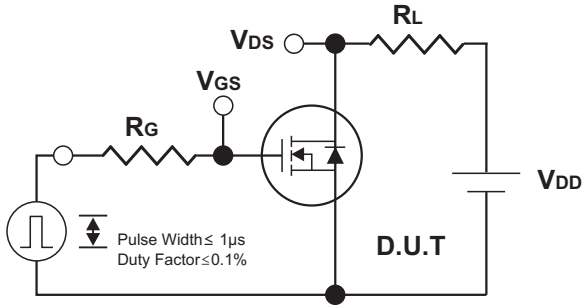
Peak Diode Recovery dv/dt Test Circuit



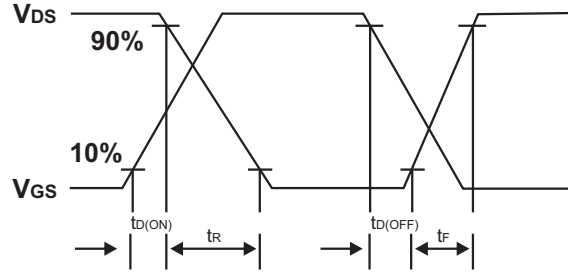
Peak Diode Recovery dv/dt Waveforms



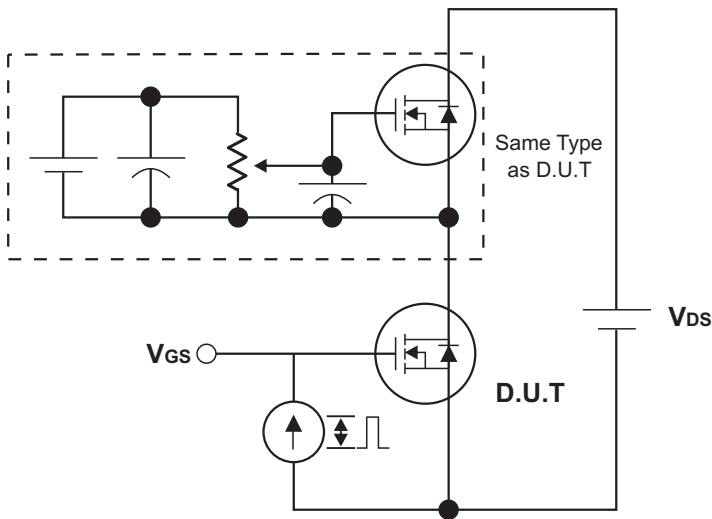
Test Circuits and waveforms



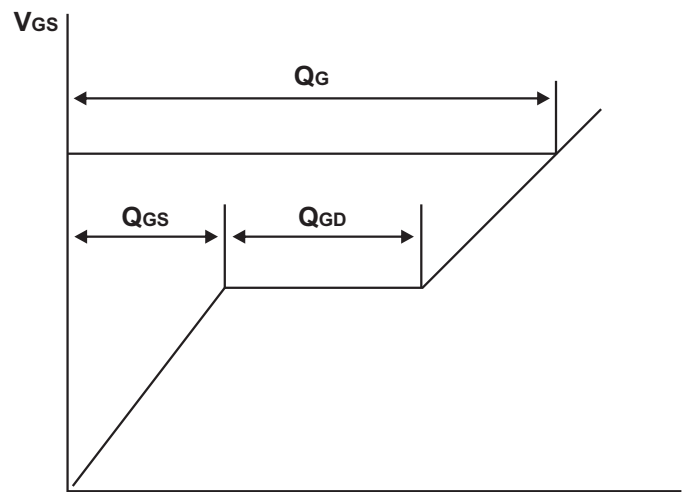
Switching Test Circuit



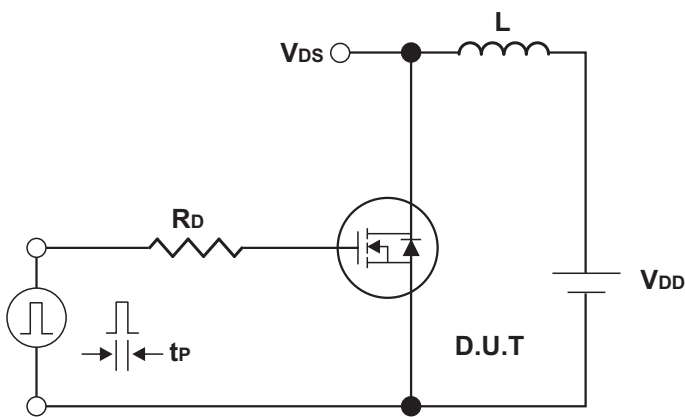
Switching Waveforms



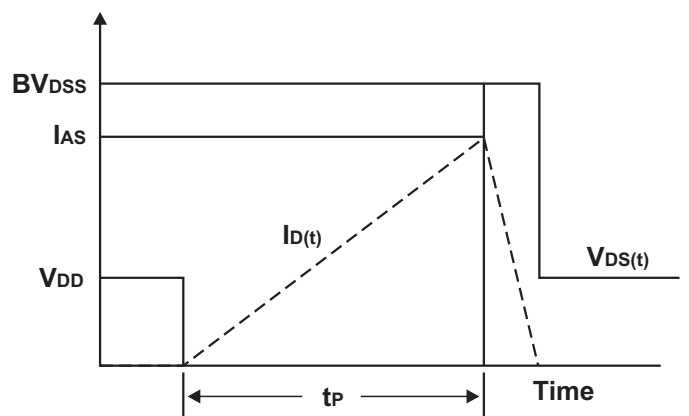
Gate Charge Test Circuit



Charge
Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms



Typical Characteristics

Fig.1 Drain Current vs. Gate-Source Voltage

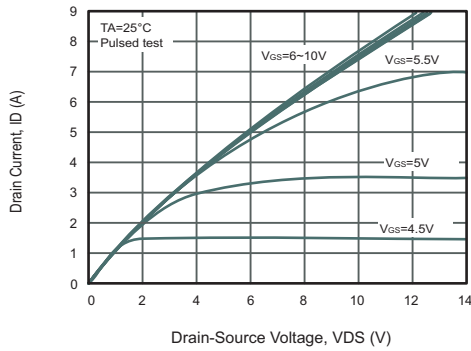


Fig.2 Drain-Source On-Resistance vs. Gate-Source Voltage

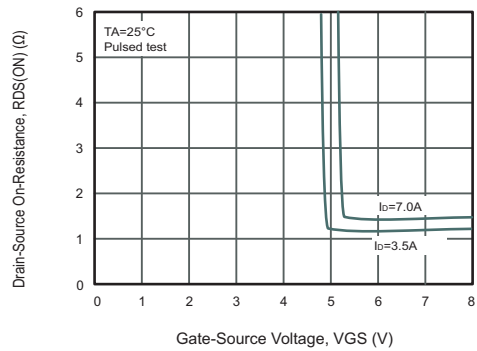


Fig.3 Gate Charge Characteristics

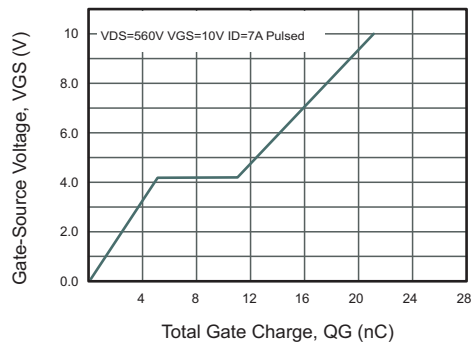


Fig.4 Capacitance Characteristics

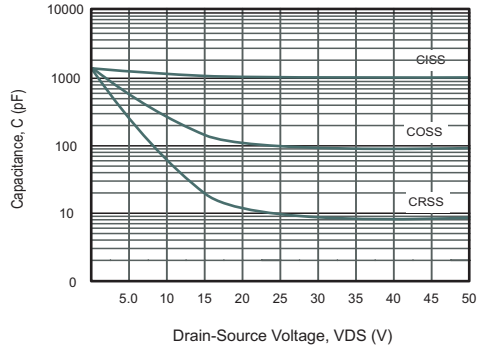


Fig.5 Drain-Source On-Resistance vs. Junction Temperature

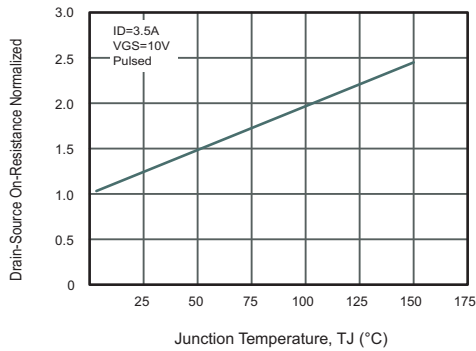


Fig.6 Breakdown Voltage vs. Junction Temperature

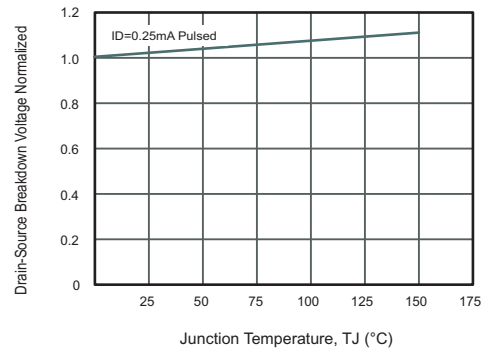


Fig.7 Gate Threshold Voltage vs. Junction Temperature

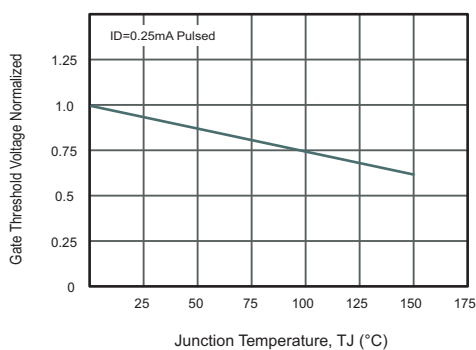
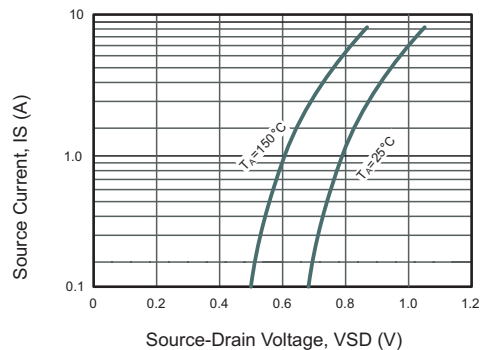


Fig.8 Source Current vs. Source-Drain Voltage





Typical Characteristics

Fig.9 Drain Current vs. Gate-Source Voltage

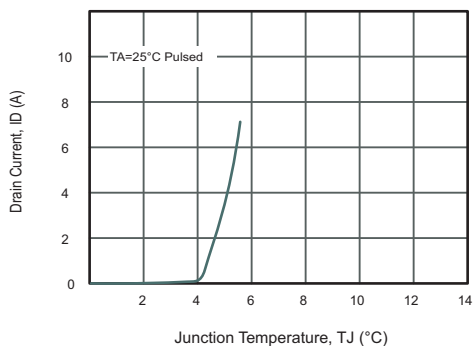


Fig.10 Drain-Source On-Resistance vs. Drain Current

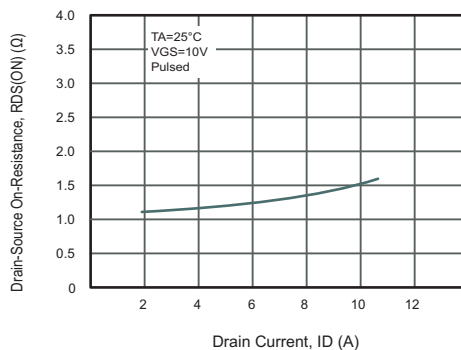


Fig.11 Power Dissipation vs. Junction Temperature

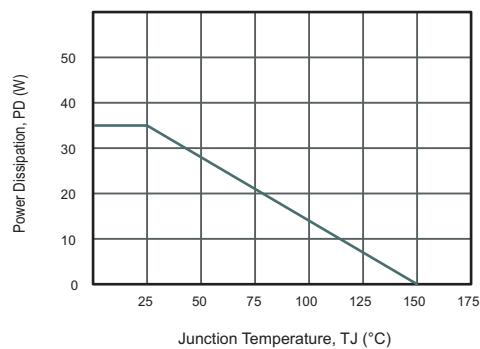


Fig.12 Drain Current vs. Junction Temperature

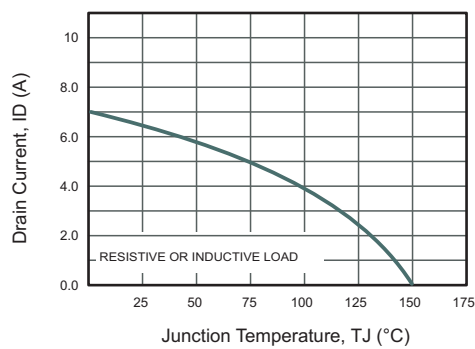
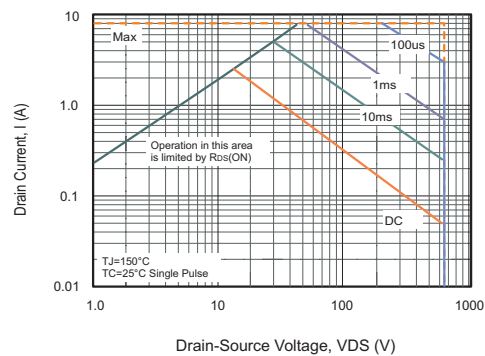
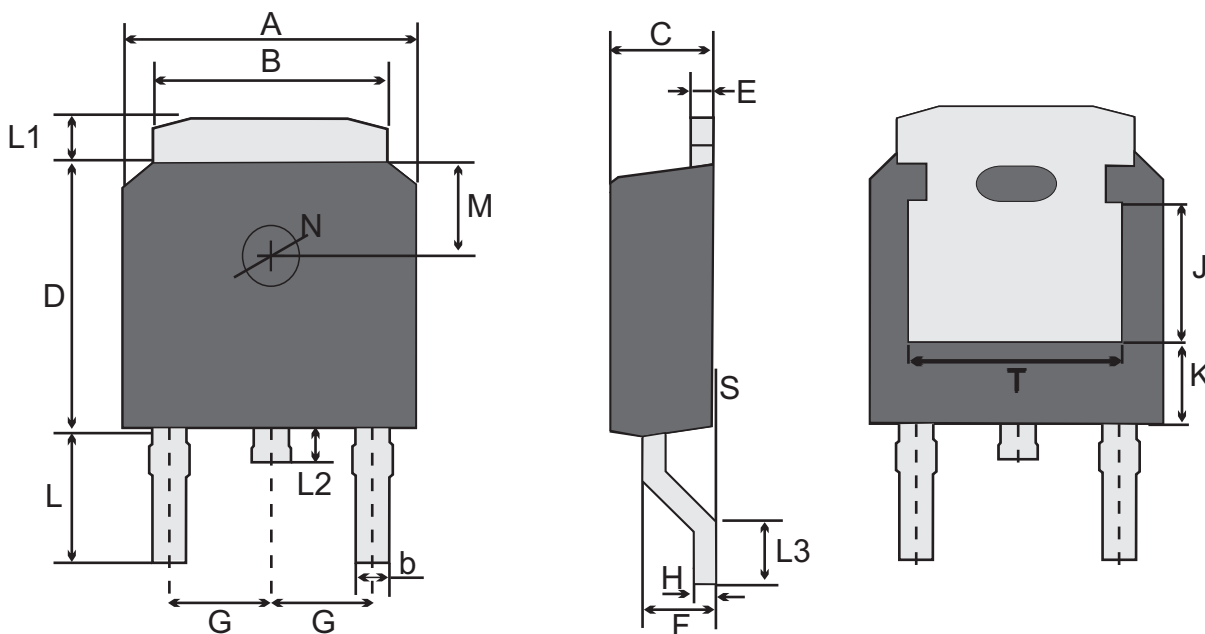


Fig.13 Safe Operating Area





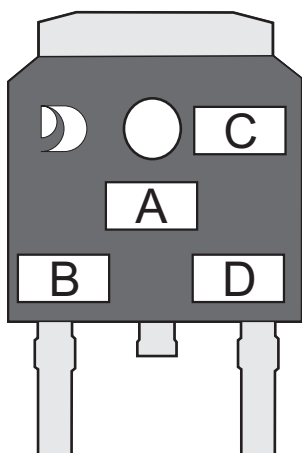
TO-252W(D-PAK) Package Outline Dimensions



TO-252W(D-PAK) mechanical data

UNIT	A	B	b	C	D	E	F	G	H	L	L1	L2	L3	S	M	N	J	K	T	
mm	max	6.7	5.5	0.8	2.5	6.3	0.6	1.8	2.29 TYPICAL	0.55	3.1	1.2	1.0	1.75	0.1	1.8 TYPICAL	1.3 TYPICAL	3.16 ref.	1.80 ref.	4.83 ref.
	typ	6.6	5.3	0.7	2.3	6.1	0.5	1.5		0.50	2.5	1.0	0.6	1.30	0.08					
	min	6.3	5.1	0.3	2.1	5.9	0.4	1.3		0.45	2.7	0.8	0.6	1.00	0.0					
mil	max	264	217	31	98	248	24	71	90 TYPICAL	22	122	47	39	69	4	71 TYPICAL	51 TYPICAL	124 ref.	71 ref.	190 ref.
	typ	260	209	28	90	240	20	59		20	98	39	24	51	3					
	min	248	201	12	83	232	16	51		18	106	31	24	55	0					

MARKING DIAGRAM



- Unmarkable Surfacea
- Marking Composition Field
- A: Marking Area
- B: Lot Code
- C: Additional Information
- D: Date Code (YWW)
- Y: Years(0~9)
- WW: Week



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[DMN1017UCP3-7](#) [EFC2J004NUZTDG](#) [P85W28HP2F-7071](#) [DMN1053UCP4-7](#) [NTE2384](#) [DMC2700UDMQ-7](#) [DMN2080UCB4-7](#)
[DMN61D9UWQ-13](#) [US6M2GTR](#) [DMN31D5UDJ-7](#) [DMP22D4UFO-7B](#) [IPS60R3K4CEAKMA1](#) [DMN1006UCA6-7](#) [DMN16M9UCA6-7](#)
[STF5N65M6](#) [IRF40H233XTMA1](#) [STU5N65M6](#) [DMN6022SSD-13](#) [DMN13M9UCA6-7](#) [DMTH10H4M6SPS-13](#) [IPS60R360PFD7SAKMA1](#)
[DMN2990UFB-7B](#) [SSM3K35CT,L3F](#) [IPLK60R1K0PFD7ATMA1](#) [2N7002W-G](#) [MCAC30N06Y-TP](#) [IPWS65R035CFD7AXKSA1](#)
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